MOSFETs Silicon N-Channel MOS

SSM6N56FE

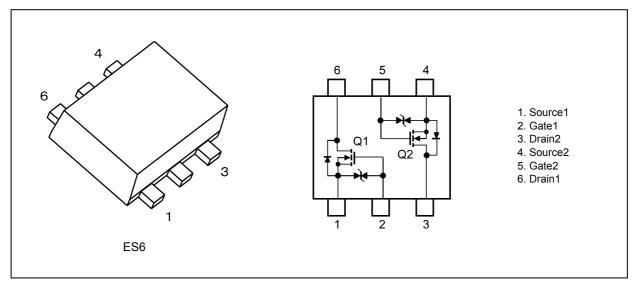
1. Applications

High-Speed Switching

2. Features

- (1) 1.5-V gate drive voltage.
- (2) Low drain-source on-resistance
 - : $R_{DS(ON)} = 235 \text{ m}\Omega \text{ (max)}$ (@V_{GS} = 4.5 V, I_D = 800 mA)
 - $R_{DS(ON)}$ = 300 m Ω (max) (@V_{GS} = 2.5 V, I_{D} = 600 mA)
 - $R_{DS(ON)}$ = 480 m Ω (max) (@V_{GS} = 1.8 V, I_D = 200 mA)
 - $\mathrm{R}_{\mathrm{DS(ON)}}$ = 840 m Ω (max) (@V_{\mathrm{GS}} = 1.5 V, I_{D} = 50 mA)

3. Packaging and Pin Assignment



Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	20	V
Gate-source voltage		V _{GSS}	±8	
Drain current (DC)	(Note 1)	I _D	800	mA
Drain current (pulsed)	(Note 1)	I _{DP}	1600]
Power dissipation	(Note 2)	PD	150	mW
Power dissipation	(Note 3)		250	1
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on an FR-4 board.(total dissipation)

- Note 3: Device mounted on an FR-4 board.(total dissipation) (25.4 mm \times 25.4 mm \times 1.6 mm ,Cu pad: 645 mm²)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

^{(25.4} mm × 25.4 mm × 1.6 mm ,Cu pad: 0.135 mm² × 6)

5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)(Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V_{DS} = 0 V, V_{GS} = ±6 V	_	_	±1	μA
Drain cut-off current		I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V	_		1	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	20	—	—	V
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	I _D = 1 mA, V _{GS} = -5 V	15	_	_	
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = 3 V, I _D = 1 mA	0.4	—	1.0	
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	I _D = 50 mA, V _{GS} = 1.5 V	—	360	840	mΩ
			I _D = 200 mA, V _{GS} = 1.8 V	_	290	480	
			I _D = 600 mA, V _{GS} = 2.5 V	_	230	300	
			I _D = 800 mA, V _{GS} = 4.5 V	_	186	235	
Forward transfer admittance	(Note 3)	Y _{fs}	V _{DS} = 3 V, I _D = 200 mA	_	1.4	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 3: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)(Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V,	_	55	_	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	6	_	
Output capacitance	C _{oss}		_	16	_	
Switching time (turn-on time)	t _{on}	V _{DS} = 10 V, I _D = 200 mA,	_	5.5	_	ns
Switching time (turn-off time)	t _{off}	V_{GS} = 0 to 2.5 V, R_{G} = 50 Ω	_	8.5	_	

5.3. Switching Time Test Circuit

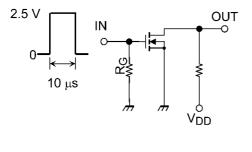


Fig. 5.3.1 Switching Time Test Circuit

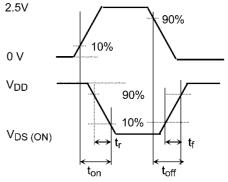


Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V _{DS} = 10 V, I _D = 800 mA,	_	1.0	_	nC
Gate-source charge 1	Q _{gs1}	V _{GS} = 4.5 V	_	0.12	_	
Gate-drain charge	Q _{gd}		_	0.4	_	

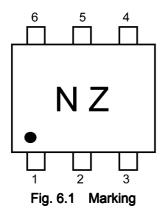
Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$. Take this into consideration when using the device.

5.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

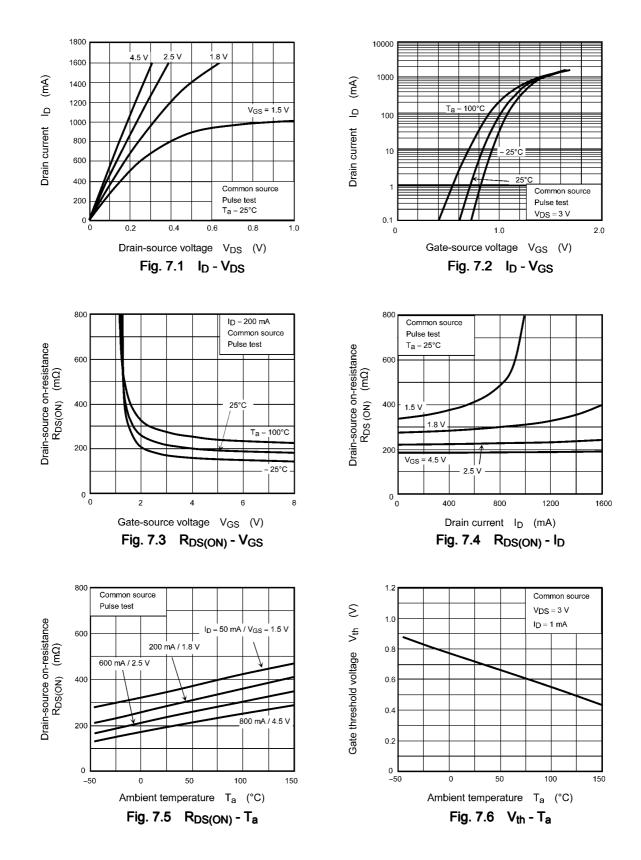
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	$I_{\rm D}$ = -0.8 A, $V_{\rm GS}$ = 0 V	_	-0.82	-1.2	V

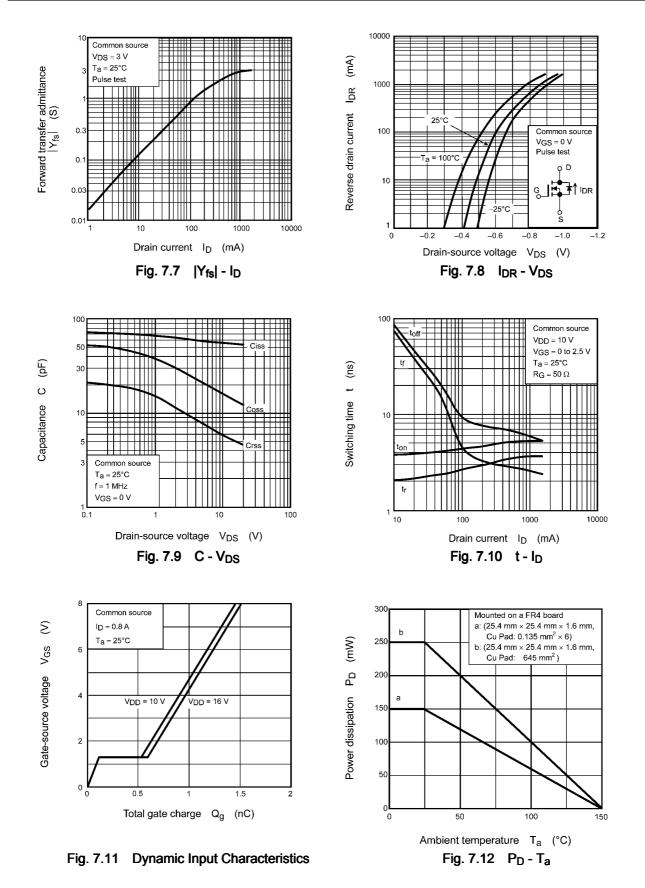
Note 1: Pulse measurement.

6. Marking



7. Characteristics Curves (Q1,Q2 Common) (Note)





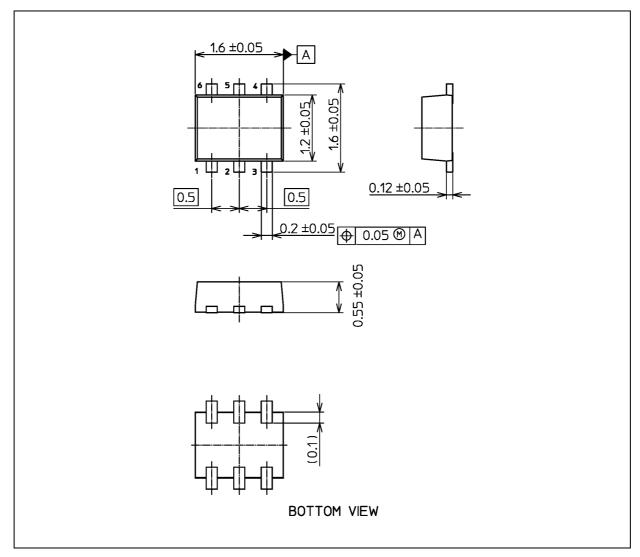
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



SSM6N56FE

Package Dimensions

Unit: mm



Weight: 3.0 mg (typ.)

Package Name(s) Nickname: ES6

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